38 Semiconductors

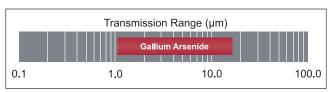
Gallium Arsenide, GaAs

Gallium Arsenide	
Crystallograph Property	ic Properties Value
Syngony	Cubic
Symmetry Class	F43m
Lattice Constants	a = 5.653
Cleavability	(111), Perfect

Mechanical Properties		
Property	Value	
Density, ρ	5.317 g/cm ³	
Knoop Hardness	721.0 kg/mm ²	
Poisson's Ratio, <i>v</i>	0.24	
Young's Modulus, E	116.0 GPa	
Shear Modulus, G	46.6 GPa	
Solubility	0.005 (25) g/100g H ₂ O (°C)	

Thermal Properties		
Property	Value	
Thermal Linear Expansion, α	5.0 × 10 ⁻⁶ /K	
Thermal Conductivity, k	54.0 W/(m•K)	
Specific Heat Capacity, $C_{\scriptscriptstyle p}$	0.345 J/(g•K)	
Melting Point, T _m	1,238 °C	

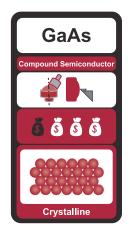
Optical Properties		
Property	Value	
Refractive Index	3.3281 @ 3.6 µm (RT)	
Refractive Index	3.2919 @ 10.6 µm (RT)	
Absorption Coefficient, A	3.00E–02 cm ⁻¹ at 10.6 μm	
dn/dT	200.0 (10 ⁻⁶ /°C) at 10.6 μm	
Transmission Range	1–15 μm	



Semiconductors 39

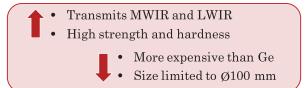
Gallium Arsenide, GaAs (cont.)

Gallium arsenide (GaAs) is a III-V compound semiconductor. It is grown by either the liquid-encapsulated Czochralski (LEC) method or the vertical gradient freeze (VGF) growth method. GaAs is available in monocrystalline or polycrystalline forms. It is available undoped as a semi-insulating material and doped with zinc, silicon, chromium, or tellurium as a semiconducting material in both p-type and n-type.



GaAs possesses low absorption from 2.5 to 12 μm. It provides an alternative to ZnSe for high-power CO₂ lasers as

lenses or mirrors. The material is nearly equal to Ge in **strength**, **hardness**, and **density** and is as easy to fabricate (diamond turn, grind, and polish). GaAs has superior thermal properties compared to CdTe.



GaAs is more expensive than ZnSe and Ge. GaAs opticalgrade material is in limited supply and is available only in the shape of flat, round blanks.

40 Semiconductors

Gallium Arsenide, GaAs (cont.)

